

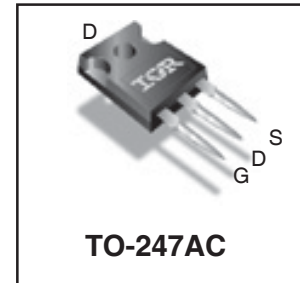
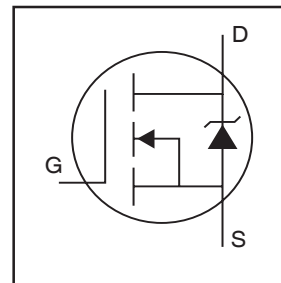
PDP MOSFET

IRFP4242PbF

Features

- Advanced process technology
- Key parameters optimized for PDP Sustain & Energy Recovery applications
- Low E_{PULSE} rating to reduce the power dissipation in Sustain & ER applications
- Low Q_G for fast response
- High repetitive peak current capability for reliable operation
- Short fall & rise times for fast switching
- 175°C operating junction temperature for improved ruggedness
- Repetitive avalanche capability for robustness and reliability

Key Parameters		
V_{DS} min	300	V
V_{DS} (Avalanche) typ.	360	V
$R_{DS(ON)}$ typ. @ 10V	49	mΩ
I_{RP} max @ $T_C = 100^\circ\text{C}$	93	A
T_J max	175	°C



G	D	S
Gate	Drain	Source

Description

This HEXFET® Power MOSFET is specifically designed for Sustain; Energy Recovery & Pass switch applications in Plasma Display Panels. This MOSFET utilizes the latest processing techniques to achieve low on-resistance per silicon area and low E_{PULSE} rating. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GS}	Gate-to-Source Voltage	±30	V
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	46	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	33	
I_{DM}	Pulsed Drain Current ①	190	
I_{RP} @ $T_C = 100^\circ\text{C}$	Repetitive Peak Current ⑤	93	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	430	W
P_D @ $T_C = 100^\circ\text{C}$	Power Dissipation	210	
	Linear Derating Factor	2.9	W/°C
T_J	Operating Junction and	-40 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature for 10 seconds	300	
	Mounting Torque, 6-32 or M3 Screw	10lb·in (1.1N·m)	N

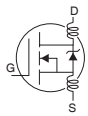
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	0.35	°C/W

Notes ① through ⑤ are on page 8

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	300	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	220	—	mV/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	49	59	m Ω	$V_{GS} = 10V, I_D = 33A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-15	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	5.0	μA	$V_{DS} = 240V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 240V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	78	—	—	S	$V_{DS} = 25V, I_D = 33A$
Q_g	Total Gate Charge	—	165	247	nC	$V_{DD} = 150V, I_D = 33A, V_{GS} = 10V$ ③
Q_{gd}	Gate-to-Drain Charge	—	61	—		
t_{st}	Shoot Through Blocking Time	100	—	—	ns	$V_{DD} = 240V, V_{GS} = 15V, R_G = 5.1\Omega$
E_{PULSE}	Energy per Pulse	—	1960	—	μJ	$L = 220nH, C = 0.4\mu F, V_{GS} = 15V$ $V_{DS} = 240V, R_G = 4.7\Omega, T_J = 25^\circ\text{C}$
		—	3740	—		$L = 220nH, C = 0.4\mu F, V_{GS} = 15V$ $V_{DS} = 240V, R_G = 4.7\Omega, T_J = 100^\circ\text{C}$
C_{iss}	Input Capacitance	—	7370	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	520	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	220	—		$f = 1.0MHz$, See Fig.9
$C_{oss\ eff.}$	Effective Output Capacitance	—	320	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 240V$
L_D	Internal Drain Inductance	—	5.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	13	—		

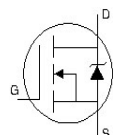


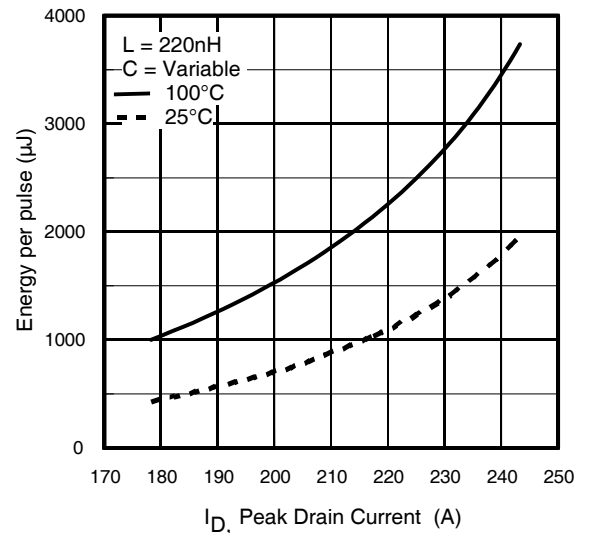
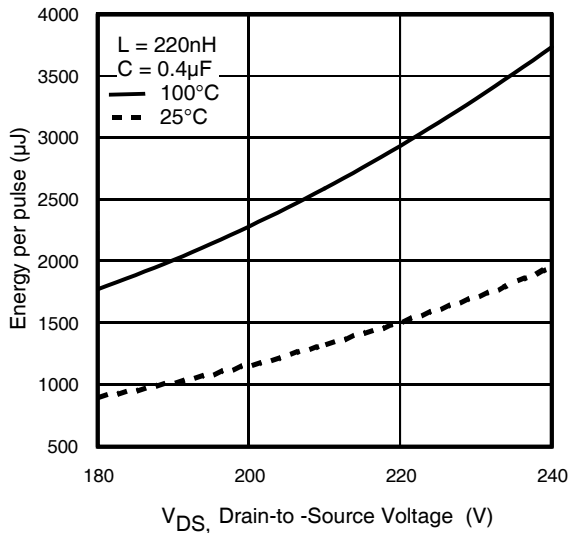
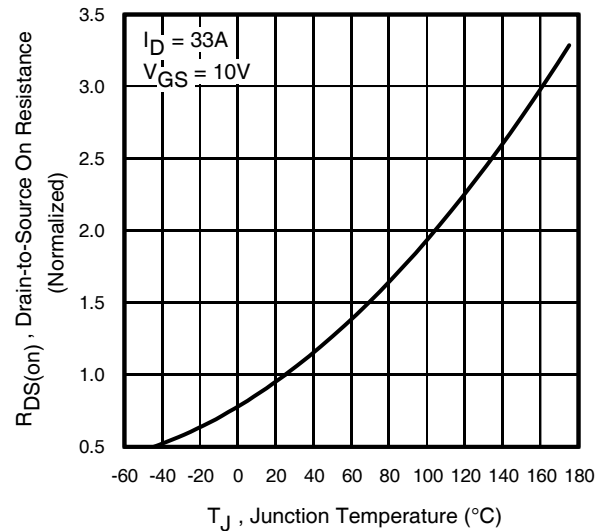
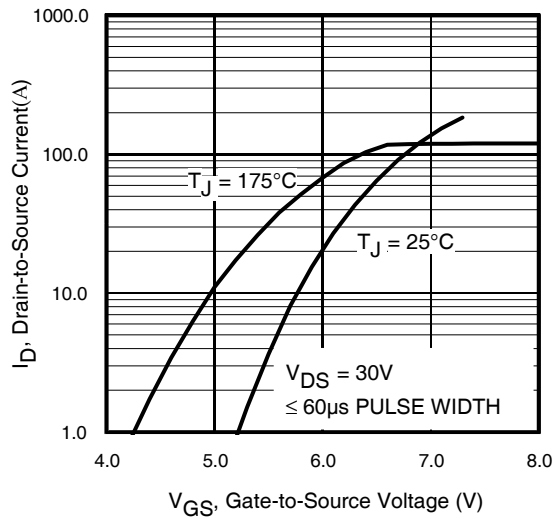
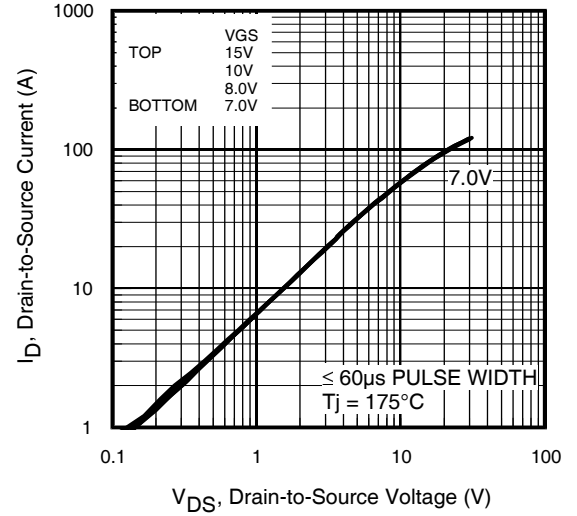
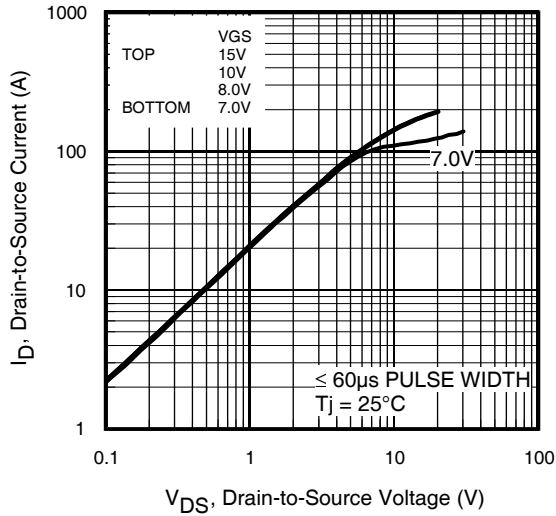
Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	700	mJ
E_{AR}	Repetitive Avalanche Energy ①	—	43	mJ
$V_{DS(Avalanche)}$	Repetitive Avalanche Voltage ①	360	—	V
I_{AS}	Avalanche Current ②	—	33	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S @ T_C = 25^\circ\text{C}$	Continuous Source Current (Body Diode)	—	—	46	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	190		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 33A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	300	450	ns	$T_J = 25^\circ\text{C}, I_F = 33A, V_{DD} = 50V$
Q_{rr}	Reverse Recovery Charge	—	2330	3500	nC	$di/dt = 100A/\mu s$ ③





IRFP4242PbF

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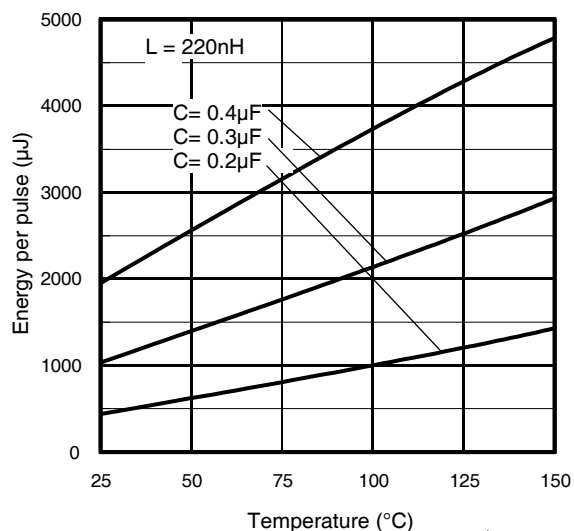


Fig 7. Typical E_{PULSE} vs. Temperature

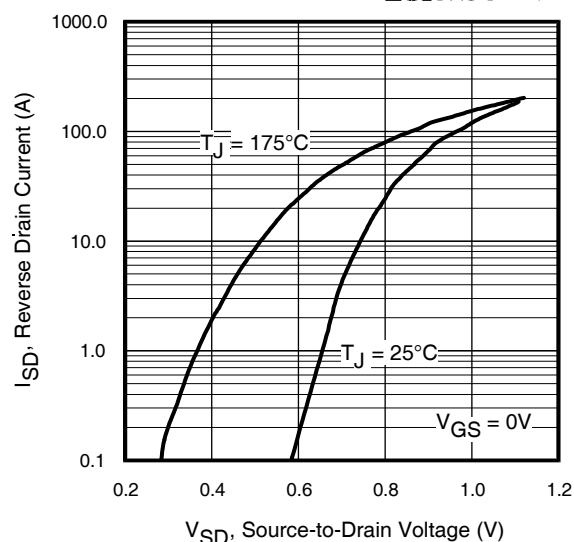


Fig 8. Typical Source-Drain Diode Forward Voltage

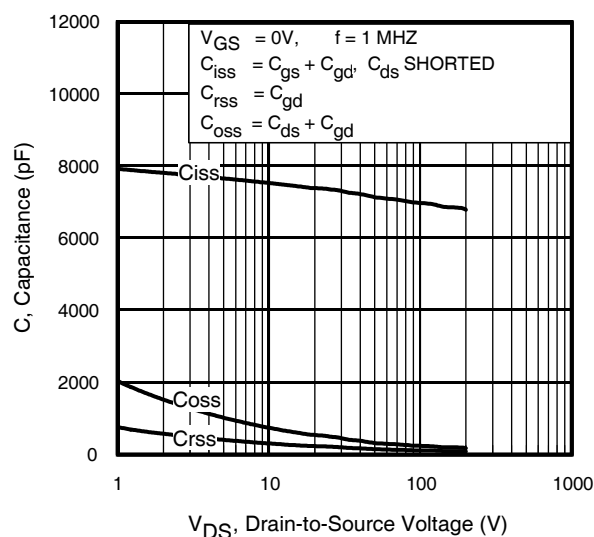


Fig 9. Typical Capacitance vs. Drain-to-Source Voltage

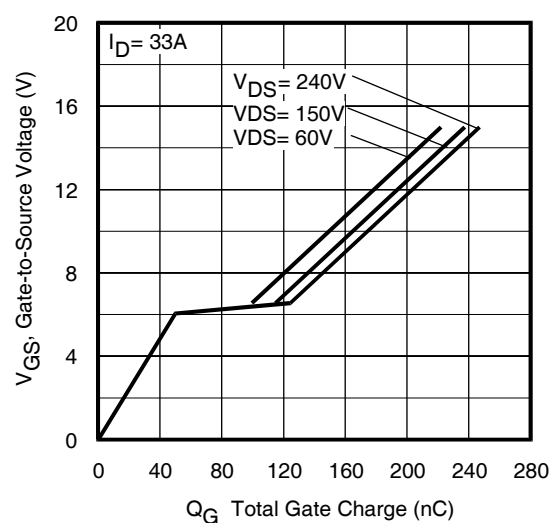


Fig 10. Typical Gate Charge vs. Gate-to-Source Voltage

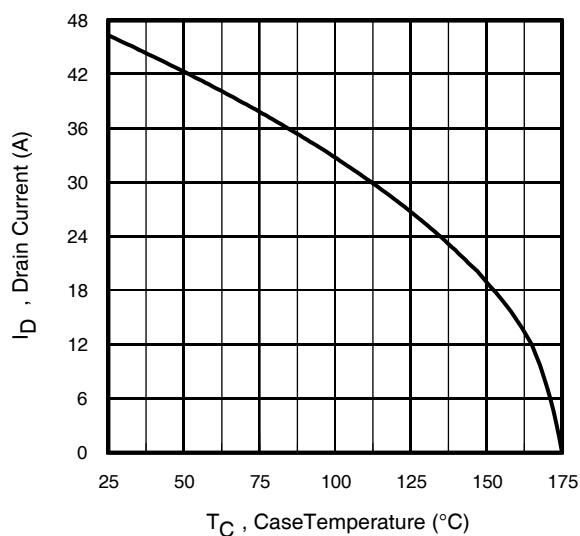


Fig 11. Maximum Drain Current vs. Case Temperature

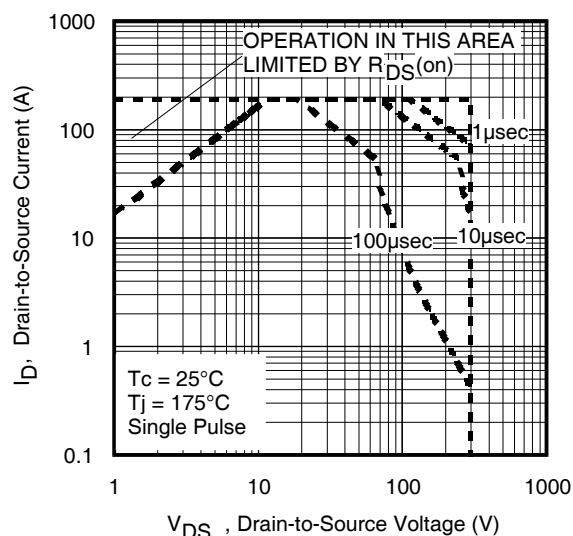
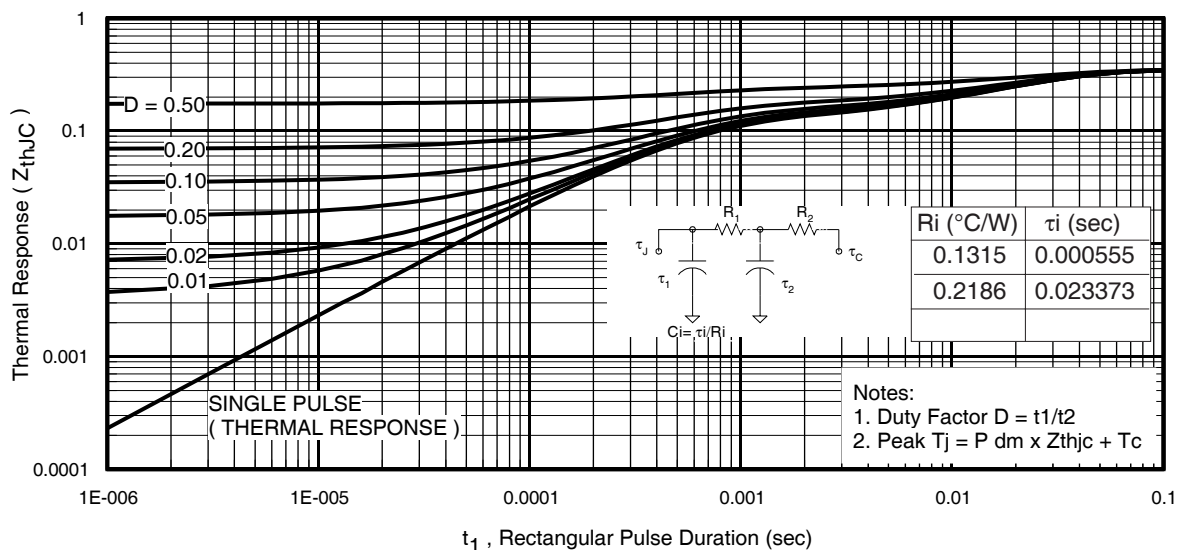
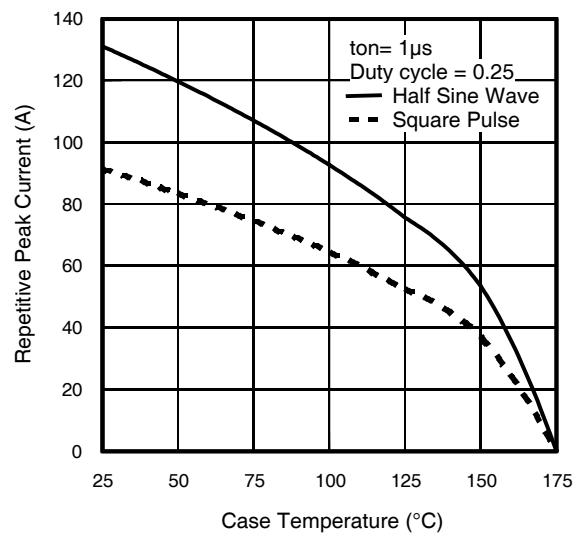
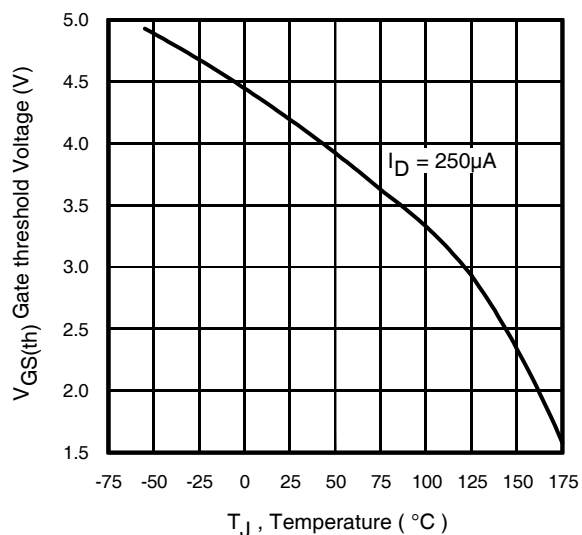
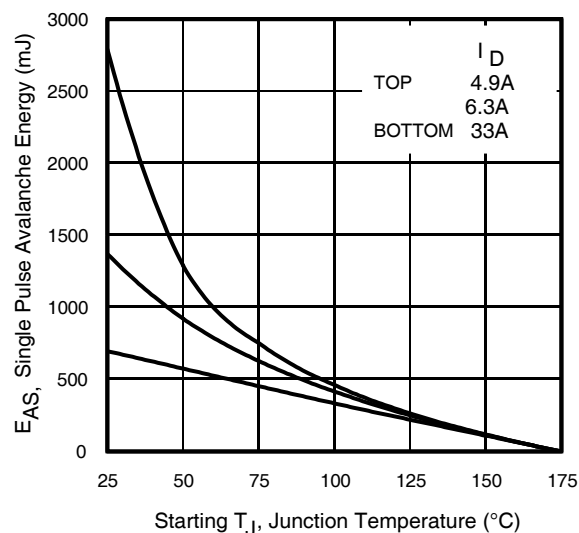
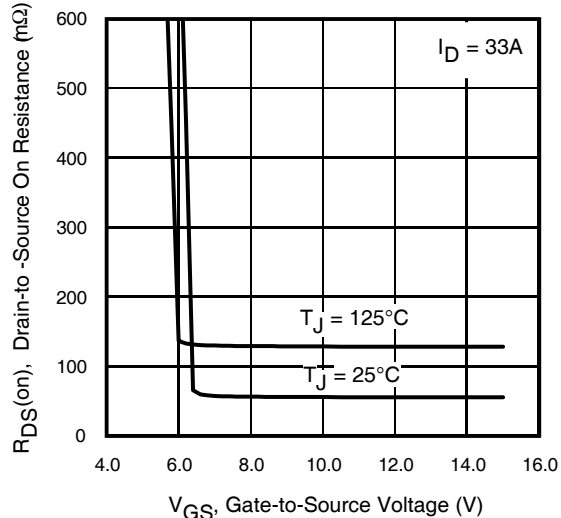


Fig 12. Maximum Safe Operating Area



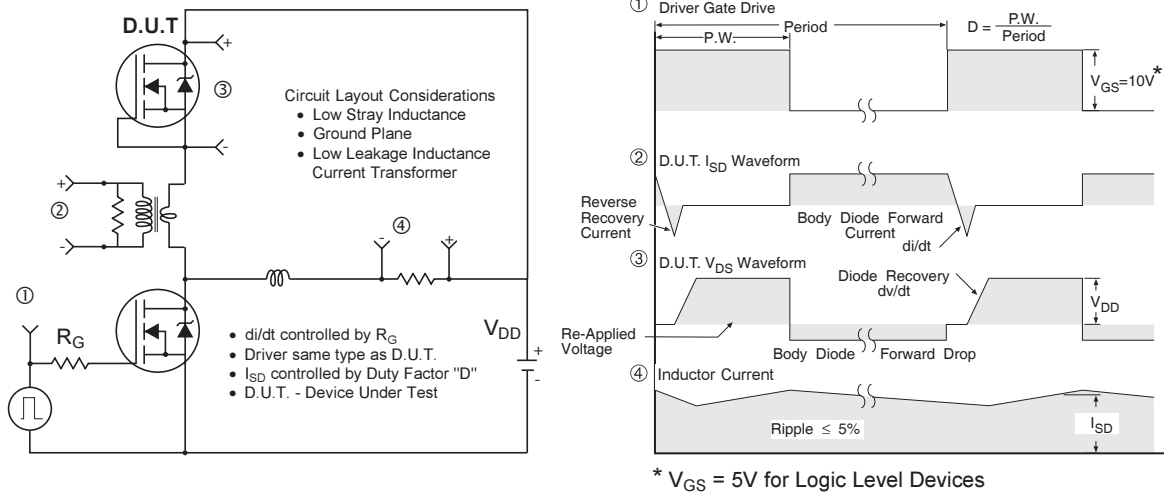


Fig 18. Diode Reverse Recovery Test Circuit for N-Channel HEXFET® Power MOSFETs

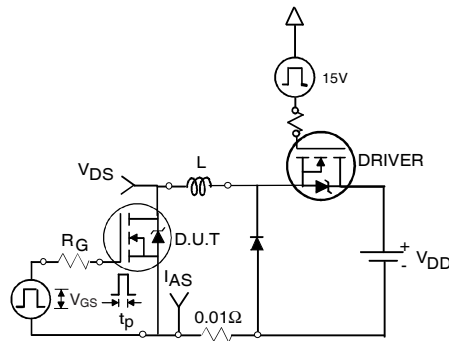


Fig 19a. Unclamped Inductive Test Circuit

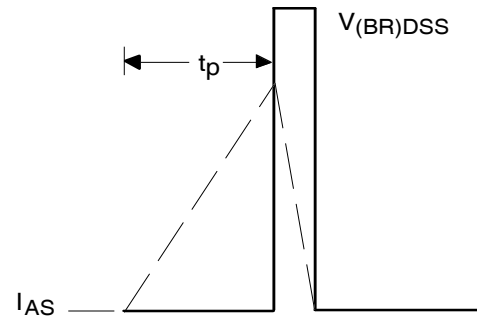


Fig 19b. Unclamped Inductive Waveforms

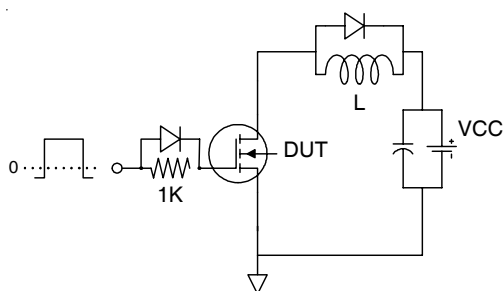


Fig 20a. Gate Charge Test Circuit

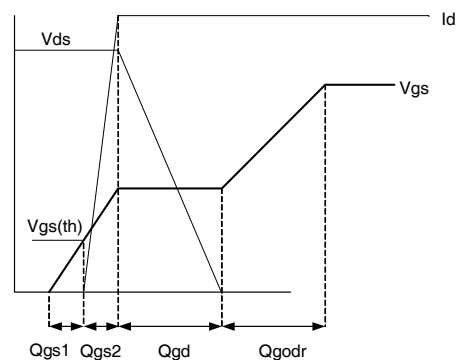


Fig 20b. Gate Charge Waveform

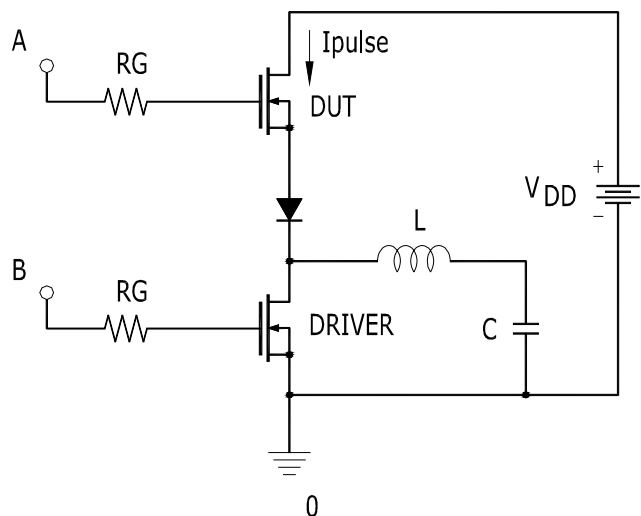


Fig 21a. t_{st} and E_{PULSE} Test Circuit

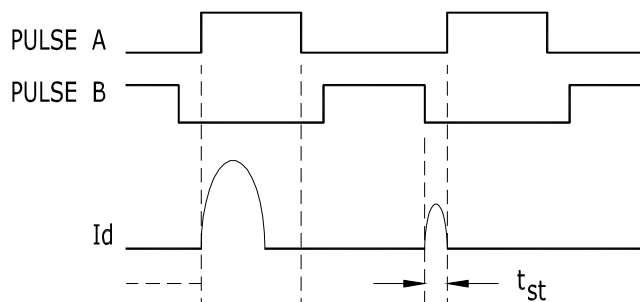


Fig 21b. t_{st} Test Waveforms

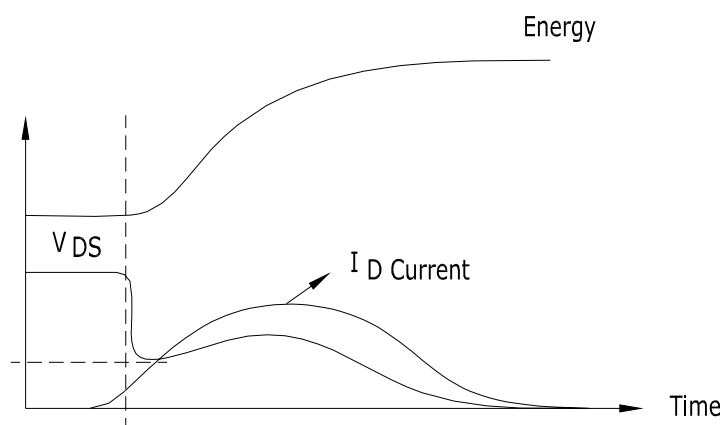


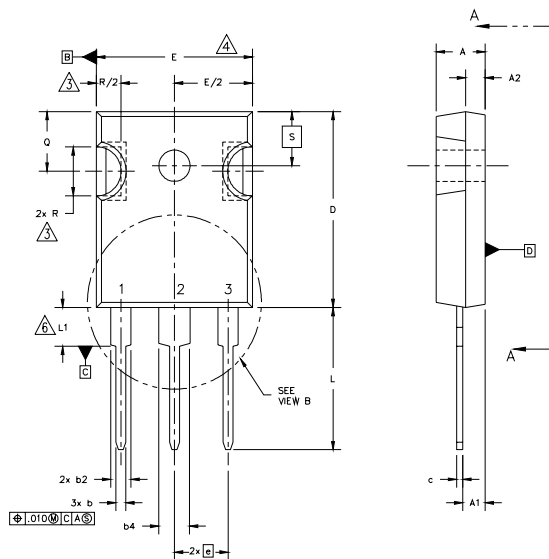
Fig 21c. E_{PULSE} Test Waveforms

IRFP4242PbF

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)

International
IR Rectifier



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ϕP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154" [3.91]
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247 WITH THE EXCEPTION OF DIMENSION c.

SYMBOL	DIMENSIONS		MIN.	MAX.	NOTES
	INCHES	MILLIMETERS			
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.37	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.034	0.38	0.86	
c1	.015	.030	0.38	0.76	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.030	0.51	0.76	
E	.602	.625	15.29	15.87	4
E1	.540	—	13.72	—	
e	.215 BSC	5.46 BSC			
ϕk	.010	2.54			
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
N	3	7.62 BSC			
ϕP	.140	.144	3.56	3.66	
Q	.209	.224	5.31	5.69	
R	.178	.216	4.52	5.49	
S	.217 BSC	5.51 BSC			

LEAD ASSIGNMENTS

HEXFET

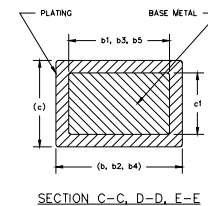
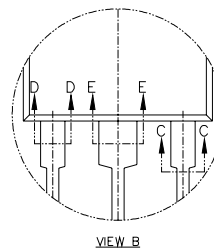
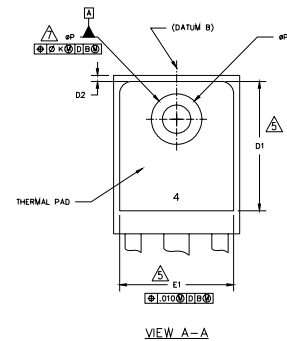
1. - GATE
2. - DRAIN
3. - SOURCE
4. - DRAIN

IGBTs, CoPACK

1. - GATE
2. - COLLECTOR
3. - EMITTER
4. - COLLECTOR

DIODES

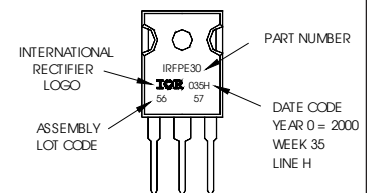
1. - ANODE/OPEN
2. - CATHODE
3. - ANODE



TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line
position indicates "Lead-Free"



TO-247AC package is not recommended for Surface Mount Application.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.28\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 33\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_θ is measured at T_J of approximately 90°C .
- ⑤ Half sine wave with duty cycle = 0.25, $t_{on} = 1\mu\text{sec}$.

Data and specifications subject to change without notice.
This product has been designed for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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